MBD701, MMBD701L, SMMBD701L

Silicon Hot-Carrier Diodes

Schottky Barrier Diodes

These devices are designed primarily for high-efficiency UHF and VHF detector applications. They are readily adaptable to many other fast switching RF and digital applications. They are supplied in an inexpensive plastic package for low-cost, high-volume consumer and industrial/commercial requirements. They are also available in a Surface Mount package.

Features

- Extremely Low Minority Carrier Lifetime 15 ps (Typ)
- Very Low Capacitance -1.0 pF @ $V_R = 20 \text{ V}$
- High Reverse Voltage to 70 V
- Low Reverse Leakage 200 nA (Max)
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS

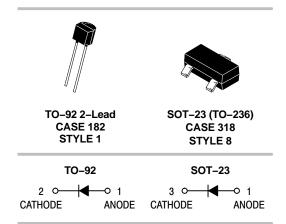
Rating	Symbol	Value	Unit
Reverse Voltage	V_{R}	70	V
Forward Power Dissipation @ T _A = 25°C MBD701 MMBD701L, SMMBD701L Derate above 25°C MBD701 MMBD701L, SMMBD701L	P _F	280 200 2.8 2.0	mW mW/°C
Operating Junction Temperature Range	TJ	-55 to +125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

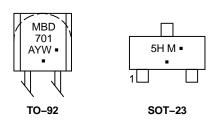


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MARKING DIAGRAMS



A = Assembly Location

Y = Year

W = Work Week

5H = Device Code (SOT-23)

M = Date Code*

■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

^{*}Date Code orientation and/or overbar may vary depending upon manufacturing location.

MBD701, MMBD701L, SMMBD701L

ELECTRICAL CHARACTERISTICS ($T_A = 25$ °C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Breakdown Voltage (I _R = 10 μAdc)	V _{(BR)R}	70	-	-	V
Total Capacitance (V _R = 20 V, f = 1.0 MHz) Figure 1	C _T	-	0.5	1.0	pF
Reverse Leakage (V _R = 35 V) Figure 3	I _R	-	9.0	200	nAdc
Forward Voltage (I _F = 1.0 mAdc) Figure 4	V _F	_	0.42	0.5	Vdc
Forward Voltage (I _F = 10 mAdc) Figure 4	V _F	-	0.7	1.0	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Device	Package	Shipping [†]
MBD701G	TO-92 (Pb-Free)	1,000 Units / Bulk
MMBD701LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBD701LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBD701LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MBD701, MMBD701L, SMMBD701L

TYPICAL ELECTRICAL CHARACTERISTICS

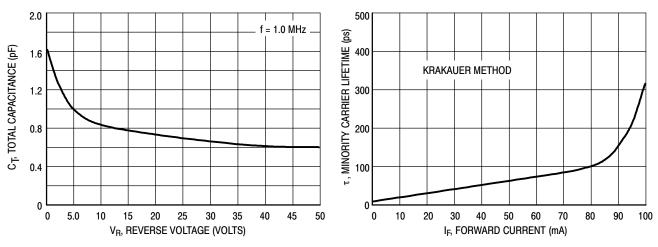


Figure 1. Total Capacitance

Figure 2. Minority Carrier Lifetime

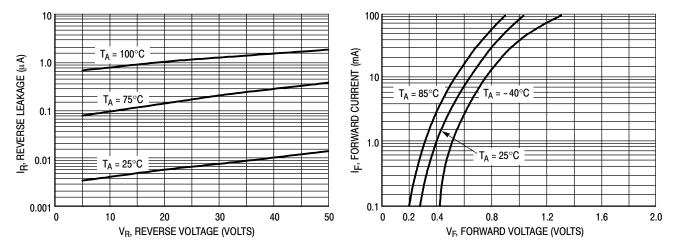


Figure 3. Reverse Leakage

Figure 4. Forward Voltage

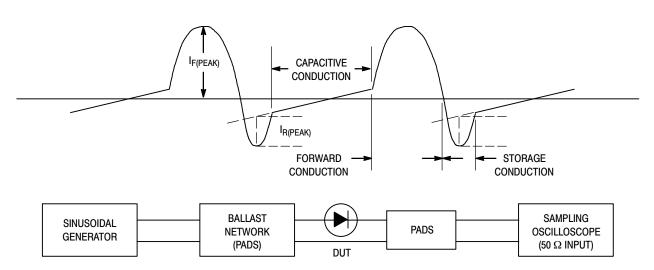


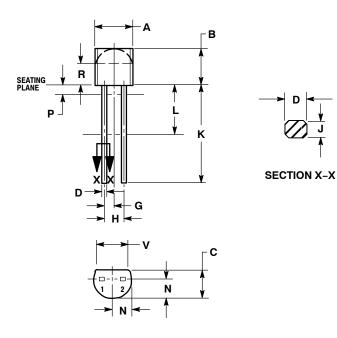
Figure 5. Krakauer Method of Measuring Lifetime



TO-92 (TO-226) CASE 182-06 **ISSUE L**

DATE 04/18/1998





- OTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND ZONE R IS UNCONTROLLED.
 4. LEAD DIMENSION IS UNCONTROLLED IN P AND

- BEYOND DIMENSION K MINIMUM.

	INCHES		CHES MILLIME		
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.21	
В	0.170 0.210		4.32	5.33	
С	0.125 0.165		3.18	4.19	
D	0.016 0.02		0.407	0.533	
G	0.050 BSC		1.27 BSC		
Н	0.100 BSC		2.54 BSC		
J	0.014 0.016		0.36	0.41	
K	0.500		12.70		
L	0.250	-	6.35		
N	0.080 0.105		2.03	2.66	
Р	0.050			1.27	
R	0.115		2.93		
٧	0.135		3.43		

STYLE 1: PIN 1. ANODE STYLE 2: PIN 1. CATHODE STYLE 3: PIN 1. MAIN TERMINAL 1 STYLE 5: PIN 1. INPUT STYLE 4: CANCELLED 2. CATHODE 2. ANODE 2. MAIN TERMINAL 2 2. OUTPUT

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DESCRIPTION	: TO-92 (TO-226)		PAGE 1 OF 1

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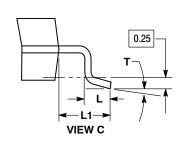


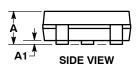
SOT-23 (TO-236) CASE 318-08 **ISSUE AS**

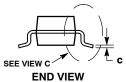
DATE 30 JAN 2018

SCALE 4:1 D - 3X b

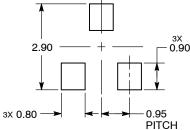
TOP VIEW







RECOMMENDED SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

STYLE 28: PIN 1. ANODE 2. ANODE

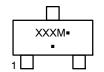
3. ANODE

NOTES:

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
- PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS				INCHES	
DIM	MIN NOM MAX			MAX MIN NOM		
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	O°		10°	O°		10°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	ı	
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE	2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE		PIN 1. NO CONNECTION	I PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE		2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE		3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE		PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE		2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN		3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION

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DESCRIPTION:	SOT-23 (TO-236)		PAGE 1 OF 1	

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STYLE 27: PIN 1. CATHODE 2. CATHODE

3. CATHODE

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